

Abstracts

p-i-n Diode Attenuator with Small Phase Shift (Short Papers)

R.J. Baeten, T.K. Ishii and J.S. Hyde. "p-i-n Diode Attenuator with Small Phase Shift (Short Papers)." 1988 Transactions on Microwave Theory and Techniques 36.4 (Apr. 1988 [T-MTT]): 789-791.

A computer-aided design technique for minimizing spurious phase shift in microstrip p-i-n diode attenuators is presented. At 9 GHz, a spurious phase shift of 0.17°/dB attenuation has been realized at 15 dB attenuation. This is better than the previous reported value of 1°/dB attenuation at comparable operating frequencies and attenuations. The diode mounting location and the dc blocking chip capacitors on microstrip are important, among other parameters, to minimize the spurious phase shift.

 [Return to main document.](#)